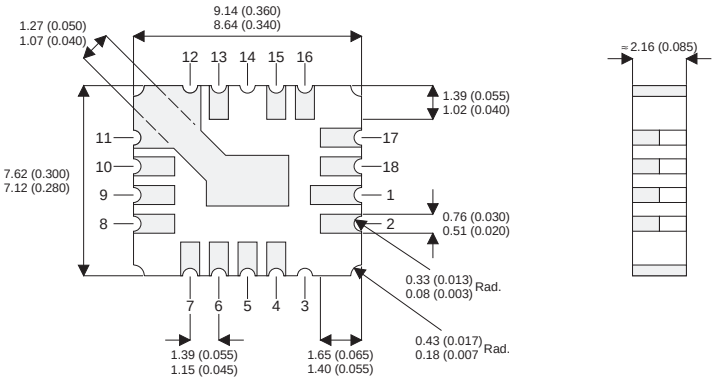
2N6845LCC4
IRFE9120

MECHANICAL DATA
Dimensions in mm (inches)



LCC4

GATE	Pins 4,5
DRAIN	Pins1,2,15,16,17,18
SOURCE	Pins 6,7,8,9,10,11,12,13

P–CHANNEL POWER MOSFET

V_{DSS}	-100V
$I_{D(cont)}$	-3.5A
$R_{DS(on)}$	0.6Ω

FEATURES

- **SURFACE MOUNT**
- **SMALL FOOTPRINT**
- **HERMETICALLY SEALED**
- **DYNAMIC dv/dt RATING**
- **AVALANCHE ENERGY RATING**
- **SIMPLE DRIVE REQUIREMENTS**
- **LIGHTWEIGHT**

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{GS}	Gate – Source Voltage	±20V
I_D	Continuous Drain Current (V_{GS} = -10V , T_{case} = 25°C)	-3.5A
I_D	Continuous Drain Current (V_{GS} = -10V , T_{case} = 100°C)	-2.2A
I_{DM}	Pulsed Drain Current [1]	-14A
P_D	Power Dissipation @ T_{case} = 25°C	14W
	Linear Derating Factor	0.09W/°C
E_{AS}	Single Pulse Avalanche Energy [2]	115mJ
dv/dt	Peak Diode Recovery [3]	-5.0V/ns
T_J , T_{stg}	Operating and Storage Temperature Range	-55 to +150°C
	Surface Temperature (for 5 sec).	300°C

Notes

1) Pulse Test: Pulse Width ≤ 300µs, δ ≤ 2%
2) @ V_{DD} = -25V , Peak I_L = -3.5A , Starting T_J = 25°C
3) @ I_{SD} ≤ -3.5A , di/dt ≤ -110A/µs , V_{DD} ≤ BV_{DSS} , T_J ≤ 150°C , Suggested R_G = 7.5Ω

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	V_{GS} = 0 I_D = -1mA	-100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C, I_D = -1mA		-0.10		V/°C
$R_{DS(on)}$	Static Drain – Source On–State Resistance [1]	V_{GS} = -10V I_D = -2.2A			0.6	Ω
		V_{GS} = -10V I_D = -3.5A			0.69	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = -250µA	-2		-4	V
g_{fs}	Forward Transconductance [1]	V_{DS} ≥ -15V I_{DS} = -2.2A	1.25			S(℧)
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0 V_{DS} = -80V			-25	µA
		T_J = 125°C			-250	
I_{GSS}	Forward Gate – Source Leakage	V_{GS} = -20V			-100	nA
I_{GSS}	Reverse Gate – Source Leakage	V_{GS} = 20V			100	
	DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	V_{GS} = 0		380		pF
C_{oss}	Output Capacitance	V_{DS} = -25V		170		
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		45		
Q_g	Total Gate Charge	V_{GS} = -10V			16.3	nC
Q_{gs}	Gate – Source Charge	I_D = -3.5A			4.7	
Q_{gd}	Gate – Drain (“Miller”) Charge	V_{DS} = -50V			9.0	
$t_{d(on)}$	Turn–On Delay Time	V_{DD} = -50V			60	ns
t_r	Rise Time	I_D = -3.5A			100	
$t_{d(off)}$	Turn–Off Delay Time	R_G = 7.5Ω			50	
t_f	Fall Time				70	
	SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current				-3.5	A
I_{SM}	Pulse Source Current [2]				-14	
V_{SD}	Diode Forward Voltage [1]	I_S = -3.5A T_J = 25°C, V_{GS} = 0			-4.8	V
t_{rr}	Reverse Recovery Time	I_F = -3.5A T_J = 25°C			200	ns
Q_{rr}	Reverse Recovery Charge [1]	d_i / d_t ≤ -100A/µs V_{DD} ≤ -50V			3.1	µC
t_{on}	Forward Turn–On Time			Negligible		
	THERMAL CHARACTERISTICS					
$R_{\theta JC}$	Thermal Resistance Junction – Case				9.1	°C/W
$R_{\theta JPC}$	Thermal Resistance Junction – PC Board				26	

Notes

1) Pulse Test: Pulse Width ≤ 300ms, δ ≤ 2%
2) Repetitive Rating – Pulse width limited by maximum junction temperature.

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